

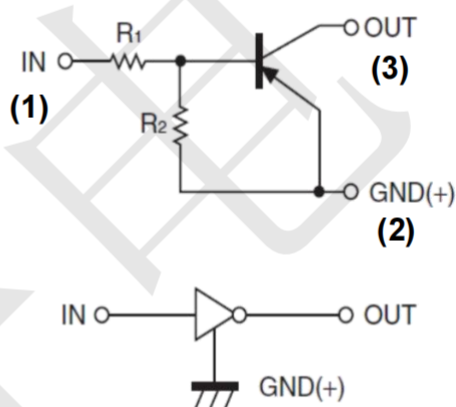
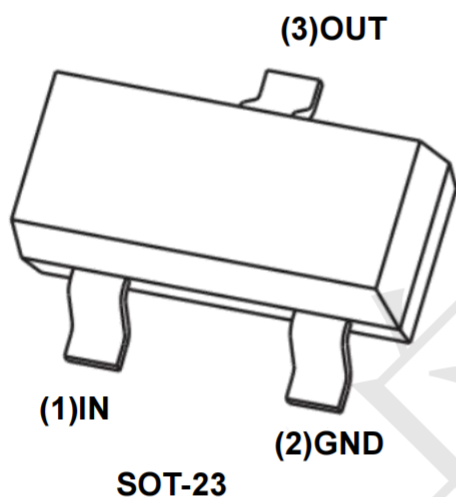
Product Summary

- $V_{CC} = -50V$
- $I_C = -100mA$
- $R_1 = 2.2k\Omega$
- $R_2 = 2.2k\Omega$

Features

- Built-in bias resistors
- making device design easy
- almost completely eliminating parasitic effects

Circuit diagram and pin information



Absolute Maximum Ratings

($T_A=25^\circ C$ unless otherwise specified)

PARAMETER	SYMBOL	LIMIT	UNIT
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	-12~+10V	V
Collector current	I_C	-100	mA
Power Total Dissipation @ $T_A=25^\circ C$	P_D	200	mW
Maximum Operating Junction Temperature	T_J	+150	$^\circ C$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ C$

Electrical Characteristics

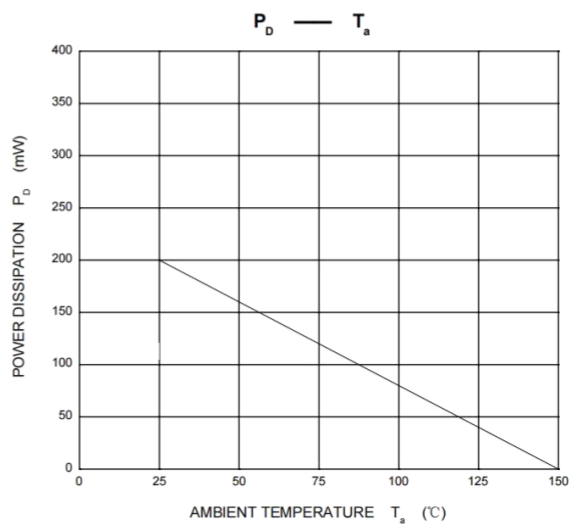
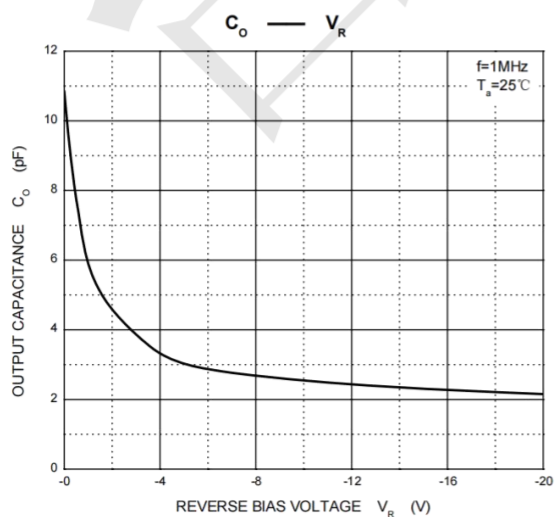
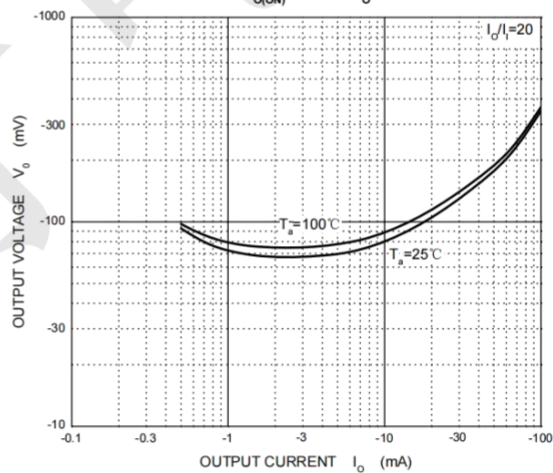
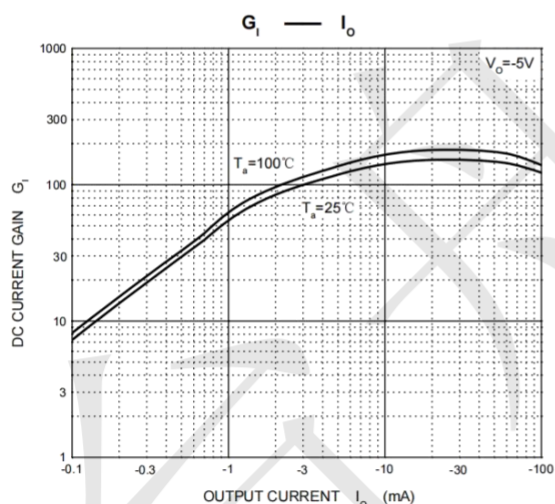
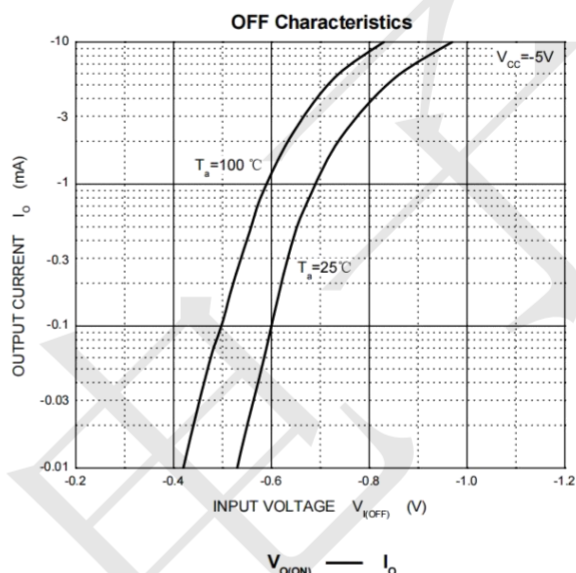
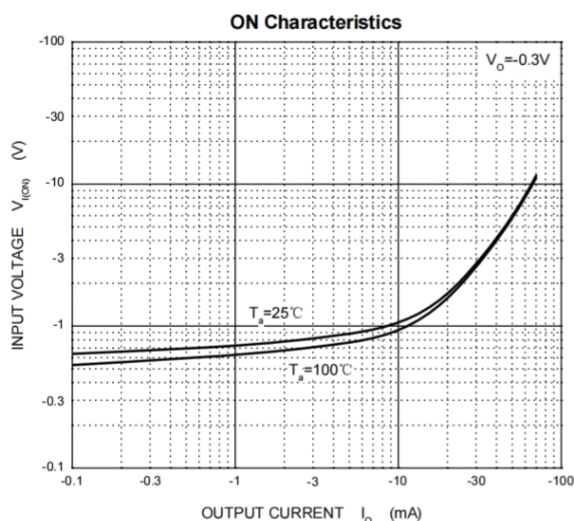
(TA=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	$V_{I(off)}$	$V_{CC}=-5V, I_O=-100\mu A$	-0.5	--	--	V
	$V_{I(on)}$	$V_O=-0.3V, I_O=-10mA$	--	--	-2.0	V
Output voltage	$V_{O(on)}$	$I_O/I_I=-10mA/-0.5mA$	--	--	-0.3	V
Input current	I_I	$V_I=-5V$	--	--	-1.8	mA
Output current	$I_{O(off)}$	$V_{CC}=-50V, V_I=0$	--	--	-0.5	μA
DC current gain	G_I	$V_O=-5V, I_O=-10mA$	80	--	--	--
Input resistance	R_1		1.5	2.2	2.9	k Ω
Resistance ratio	R_2/R_1		0.8	1.0	1.2	--
Transition frequency	f_T	$V_O=-10V, I_O=-5mA,$ $=100MHz$	--	250	--	MHz

Note:

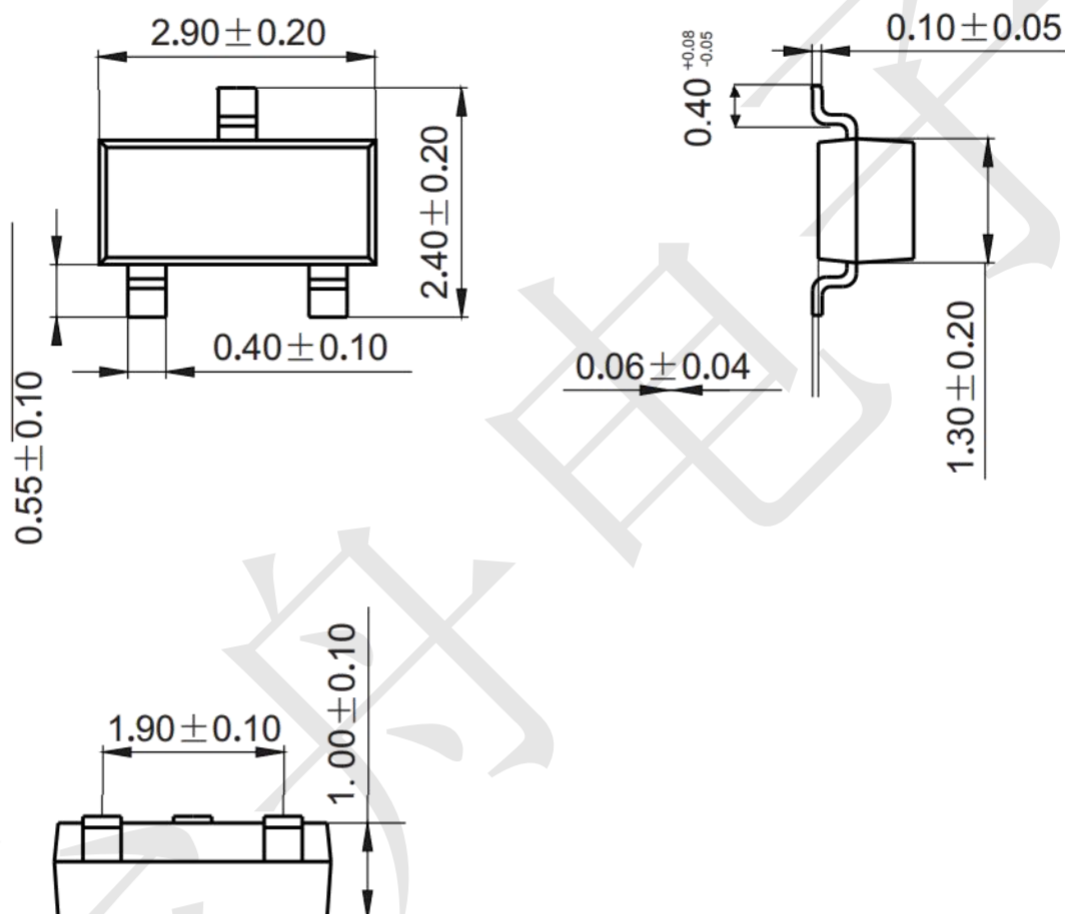
- 1.Characteristics of built-in transistor
- 2.Each terminal mounted on a reference land

Typical Performance Characteristics(TA=25°C)



Package Outline Dimensions (unit: mm)

SOT-23



Mounting Pad Layout (unit: mm)

